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(54) 3D MEMORY DEVICE WITH A DRAM CHIP

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ABSTRACT (57)

A 3D memory device includes a first die of a 3D memory structure and a second die bonded with the first die. The second die includes DRAM cells. The 3D memory structure includes memory cells in a conductor/insulator stack. The conductor/insulator stack has conductive layers and dielectric layers alternatingly stacked over each other.

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